NANOSTRUCTURE FORMATION OF $As_x Se_{100-x}$ AND $Ge_x Sb_{100-x}$ AMORPHOUS FILMS UNDER CONDITIONS OF DISCRETE THERMAL EVAPORATION

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S u m m a r y

We present the results of investigations by electron microscopy of a nanostructure of amorphous thin films of the As – Se and Ge – Sb systems. The dependence of a level microinhomogeneity of samples on its chemical structure and technological conditions of evaporation is found. The dependence of a nanostructure of films on the energy of adsorbed particles and composition of the vapor phase is revealed.